## ABSTRACT

The present invention is a method of forming a channel device. The method comprises the steps of providing at least one active region on a substrate wherein the active region comprises a plurality of discontinuous gate structures. The method further comprises providing an ion implantation in the substrate. In accordance with the present invention, a higher Early Voltage is achieved thereby enabling halo/pocket and LDD implants to be effectively utilized in the design of analog circuitry.

F0056 1663P -11-